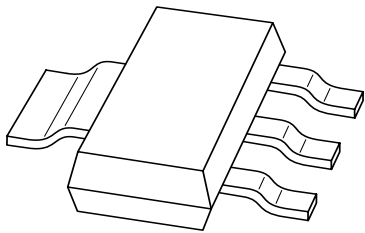


# DATA SHEET



## **PZTA42** NPN high-voltage transistor

Product data sheet  
Supersedes data of 1997 Jun 16

1999 May 21

# NPN high-voltage transistor

# PZTA42

## FEATURES

- Low current (max. 100 mA)
- High voltage (max. 300 V).

## APPLICATIONS

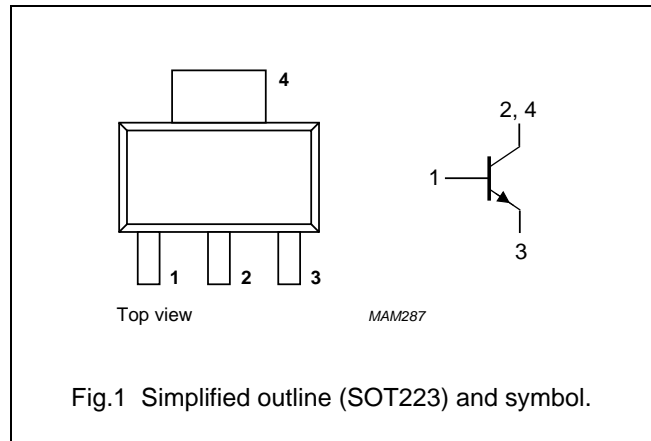
- Telephony and professional communication equipment.

## DESCRIPTION

NPN high-voltage transistor in a SOT223 plastic package.  
PNP complement: PZTA92.

## PINNING

PIN	DESCRIPTION
1	base
2,4	collector
3	emitter



## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	300	V
$V_{CEO}$	collector-emitter voltage	open base	–	300	V
$V_{EBO}$	emitter-base voltage	open collector	–	6	V
$I_C$	collector current (DC)		–	100	mA
$I_{CM}$	peak collector current		–	200	mA
$I_{BM}$	peak base current		–	100	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$ ; note 1	–	1.2	W
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C
$T_{amb}$	operating ambient temperature		–65	+150	°C

## Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>. For other mounting conditions, see “*Thermal considerations for SOT223 in the General Part of associated Handbook*”.

## NPN high-voltage transistor

PZTA42

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	104	K/W
$R_{th\ j-s}$	thermal resistance from junction to soldering point		23	K/W

## Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>. For other mounting conditions, see "Thermal considerations for SOT223 in the General Part of associated Handbook".

## CHARACTERISTICS

$T_{amb} = 25\text{ °C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$I_{CBO}$	collector cut-off current	$I_E = 0; V_{CB} = 200\text{ V}$	–	20	nA
$I_{EBO}$	emitter cut-off current	$I_C = 0; V_{BE} = 6\text{ V}$	–	100	nA
$h_{FE}$	DC current gain	$V_{CE} = 10\text{ V}$ $I_C = 1\text{ mA}$ $I_C = 10\text{ mA}$ $I_C = 30\text{ mA}$	25 40 40	– – –	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 20\text{ mA}; I_B = 2\text{ mA}$	–	500	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 20\text{ mA}; I_B = 2\text{ mA}$	–	900	mV
$C_{re}$	feedback capacitance	$I_C = i_c = 0; V_{CB} = 20\text{ V}; f = 1\text{ MHz}$	–	3	pF
$f_T$	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 20\text{ V}; f = 100\text{ MHz}$	50	–	MHz

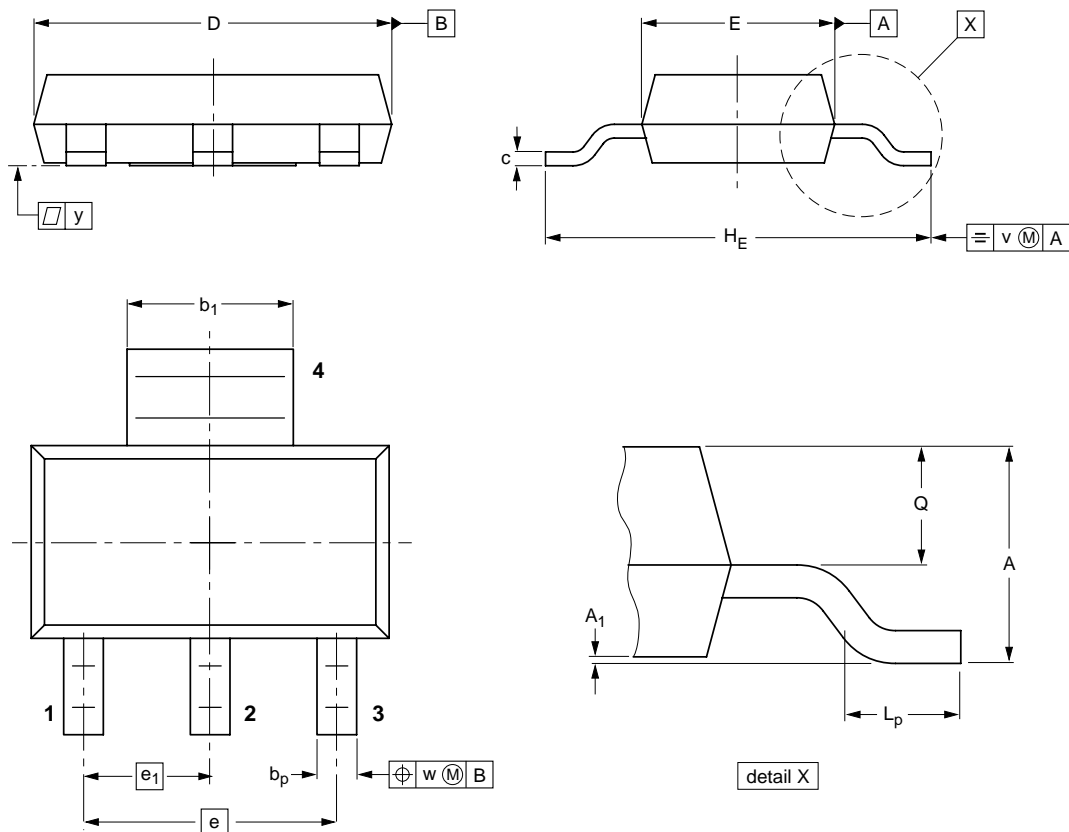
# NPN high-voltage transistor

PZTA42

## PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b <sub>p</sub>	b <sub>1</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w	y
mm	1.8 1.5	0.10 0.01	0.80 0.60	3.1 2.9	0.32 0.22	6.7 6.3	3.7 3.3	4.6	2.3	7.3 6.7	1.1 0.7	0.95 0.85	0.2	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT223			SC-73			97-02-28 99-09-13